

AMENDMENTS TO THE CLAIMS

1. – 12. (Canceled)

13. (Original) A method of fabricating a dielectric material, said method comprising:

incorporating a Group V element in a Group III metal oxide.

14. (Original) A method according to claim 13, wherein said Group III metal oxide is aluminum oxide.

15. (Original) A method according to claim 13, wherein said Group V element is selected from the group consisting of nitrogen and phosphorous.

16. (Original) A method according to claim 14, wherein said Group V element is selected from the group consisting of nitrogen and phosphorous.

17. (Original) A method according to claim 13, wherein said dielectric material is deposited in an atmosphere comprising a mixture of oxygen and nitrogen.

18. (Original) A method according to claim 17, wherein said mixture of oxygen and nitrogen has an oxygen-to-nitrogen ratio ranging from 24:6 to 9:21.

19. (Original) A method according to claim 17, wherein said mixture of oxygen and nitrogen has an oxygen-to-nitrogen ratio of 18:12.

20. (Original) A method according to claim 13, wherein said dielectric material is deposited in an atmosphere comprising a mixture of oxygen and phosphorous.

21. (Original) A method according to claim 13, wherein said dielectric material is formed by a technique selected from the group consisting of reactive sputtering, annealing, atomic layer deposition (ALD), chemical vapor deposition (CVD), metalorganic chemical vapor deposition (MOCVD), plasma nitridation, and oxidation of metal nitrides.

22. (Original) A method according to claim 13, wherein said Group V element is incorporated by annealing the Group III metal oxide in the presence of a gas selected from the group consisting of N_2O , NO, and NH_3 .

23. (Original) A method according to claim 13, wherein said Group V element is incorporated by atomic layer deposition of the Group III metal oxide in the presence of a gas selected from the group consisting of N_2O , NO, and NH_3 .

24. (Original) A method according to claim 13, wherein said Group V element is incorporated by chemical vapor deposition of the Group III metal oxide in the presence of a gas selected from the group consisting of N_2O , NO, and NH_3 .

25. (Original) A method according to claim 13, wherein said Group V element is incorporated by plasma nitridation of the Group III metal oxide.

26. (Original) A method according to claim 13, wherein said Group V element is incorporated by oxidation of a metal nitride.